PROCESS CP211

Power Transistor

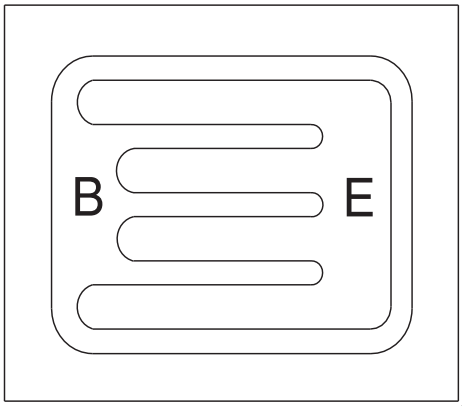
NPN - Amp/Switch Transistor Chip

Central™ Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL BASE
Die Size	80 x 99 MILS
Die Thickness	12.5 MILS
Base Bonding Pad Area	12 x 32 MILS
Emitter Bonding Pad Area	13 x 48 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Cr/Ni/Ag 16,000Å

GEOMETRY



BACKSIDE COLLECTOR

R0

GROSS DIE PER 4 INCH WAFER

1,450

PRINCIPAL DEVICE TYPES

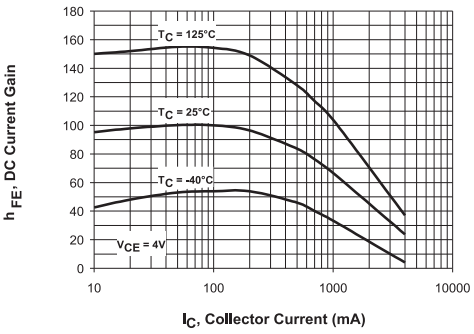
2N3054A
CJD41C
TIP41C

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

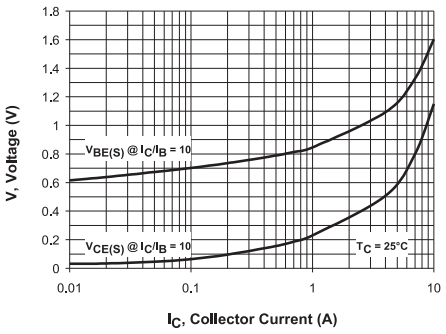
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Typical Electrical Characteristics

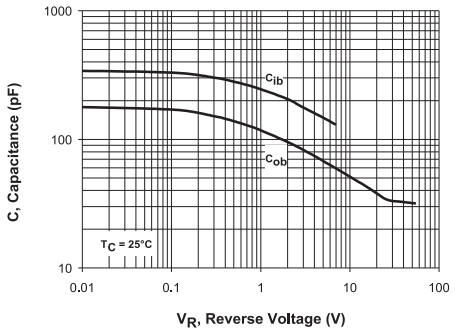
DC Current Gain



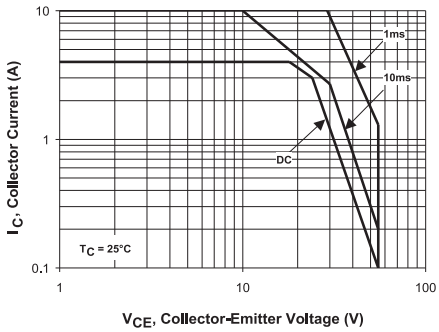
"ON" Voltage



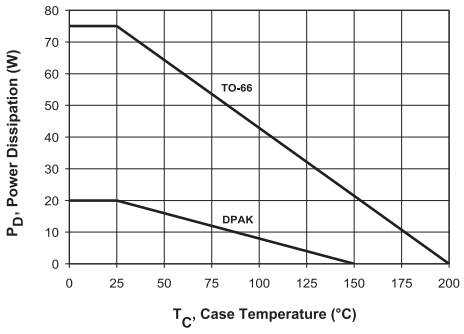
Capacitance



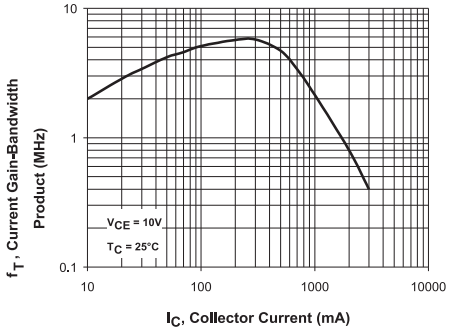
Safe Operating Area



Power Derating



Current Gain-Bandwidth Product



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